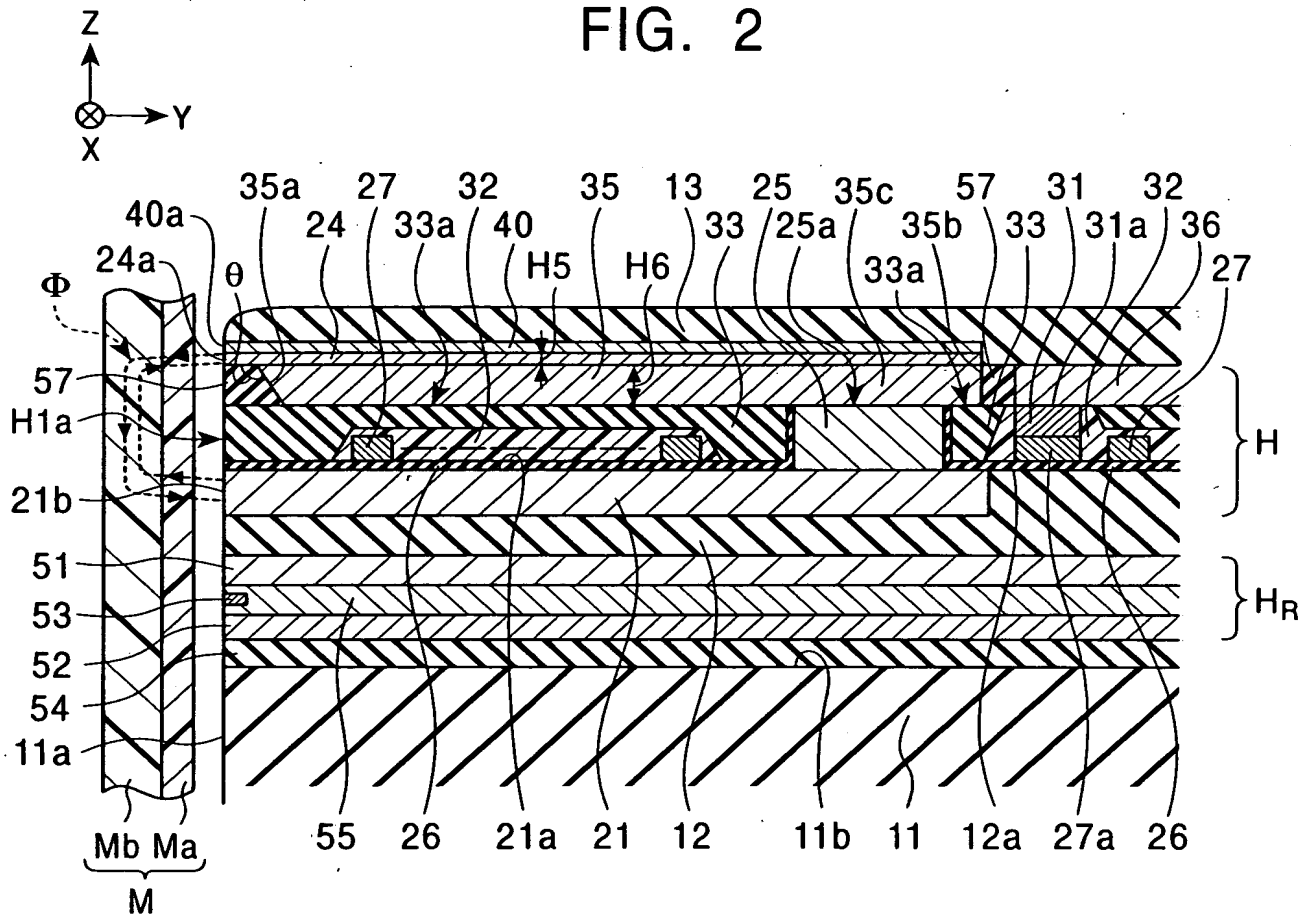
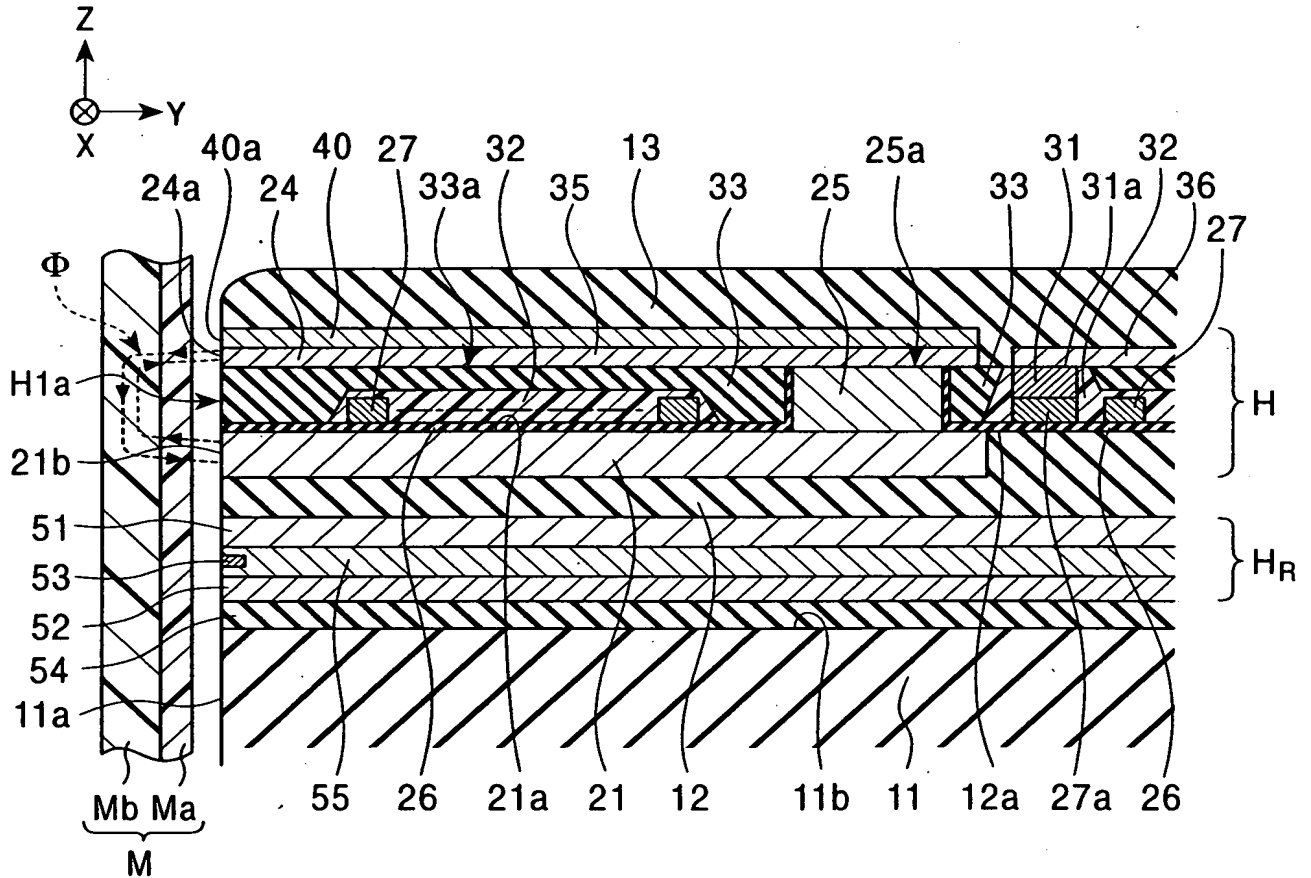


FIG. 2



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FIG. 3



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FIG. 4

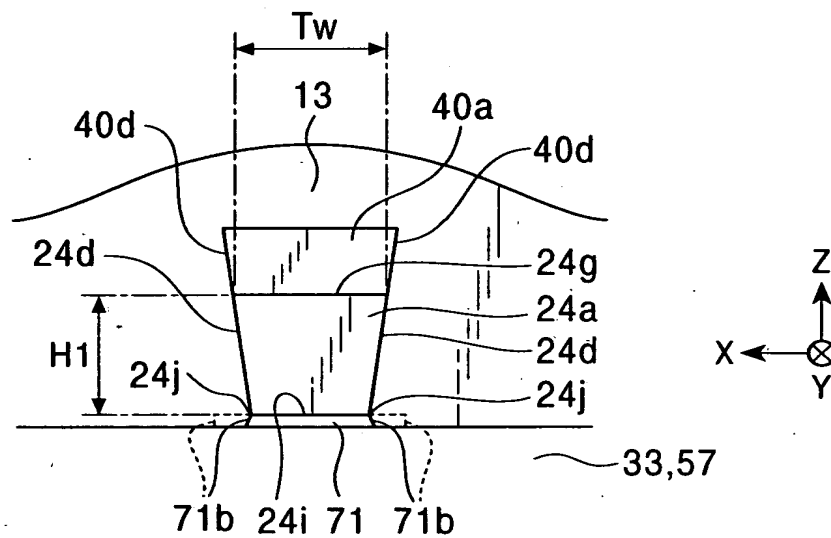


FIG. 5

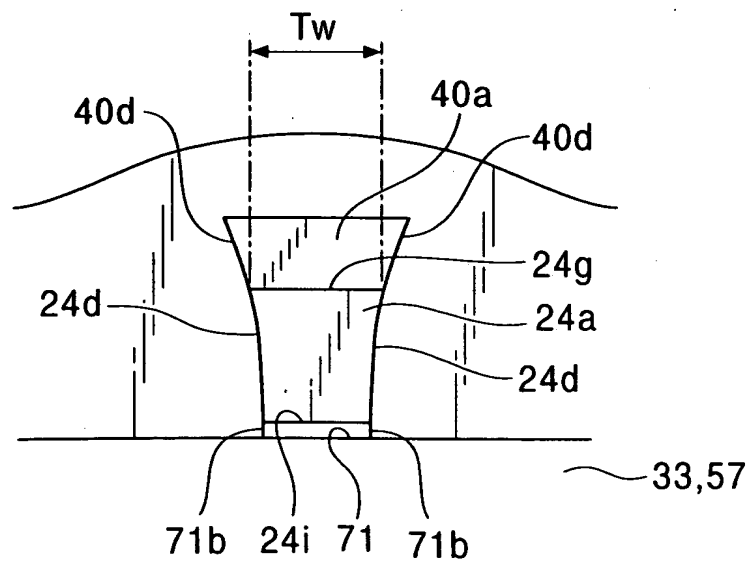


FIG. 6

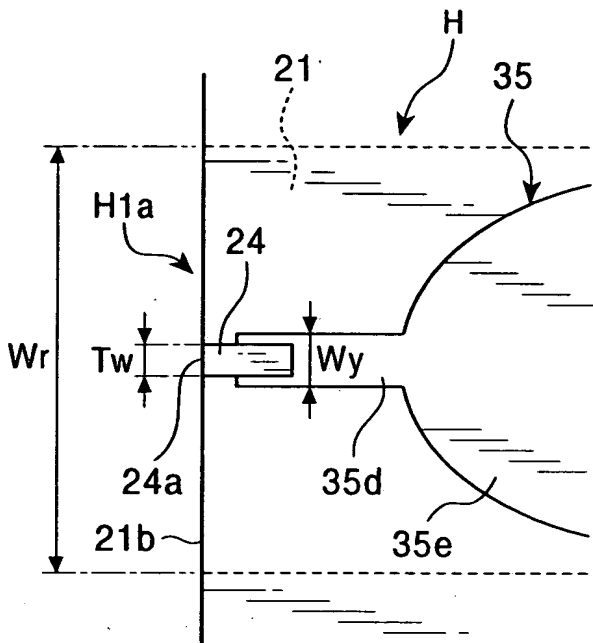
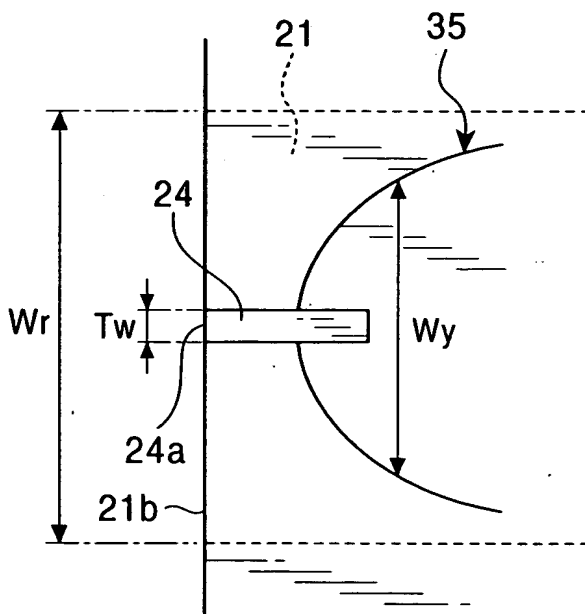


FIG. 7



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FIG. 8

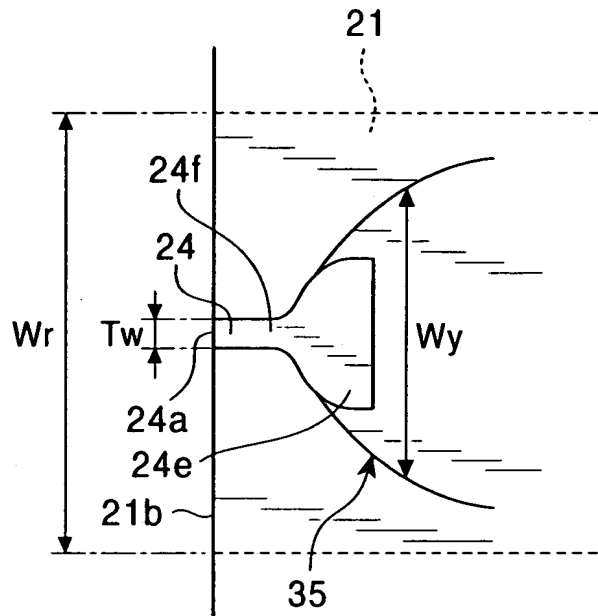
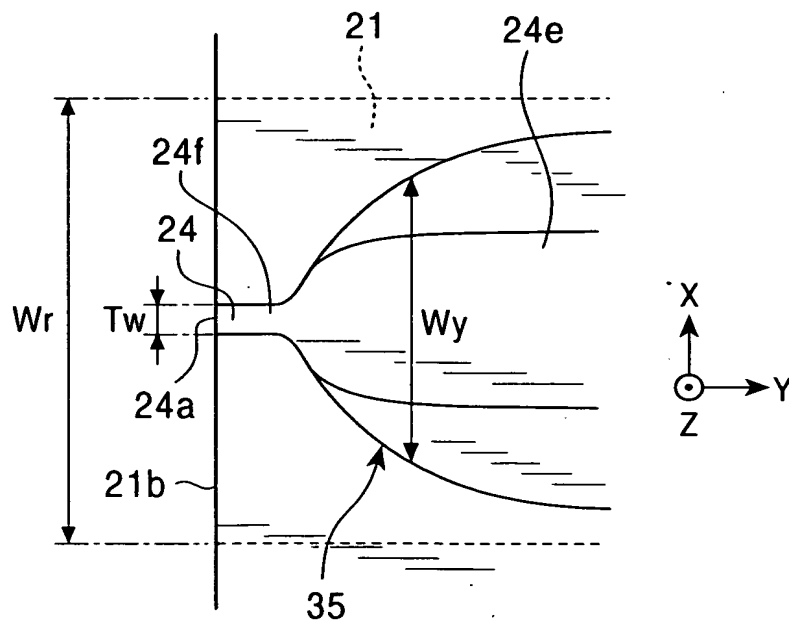


FIG. 9



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FIG. 10

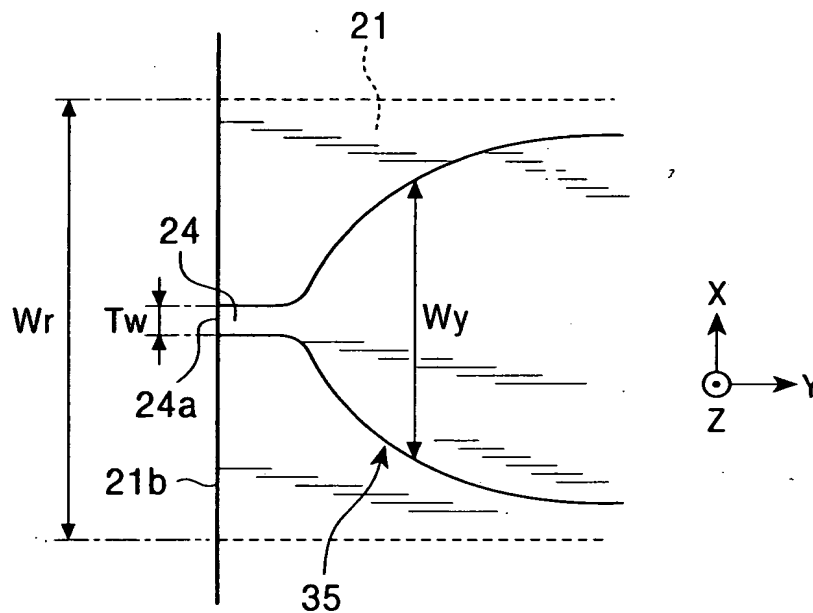
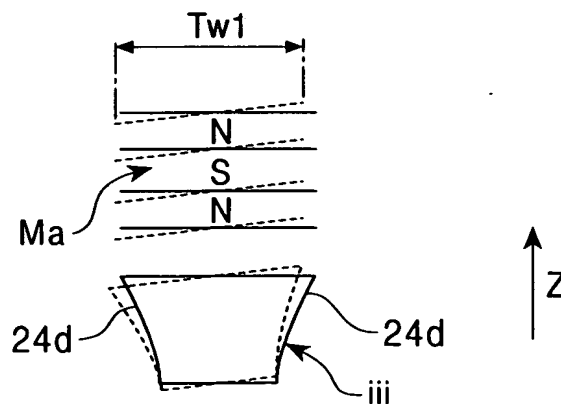


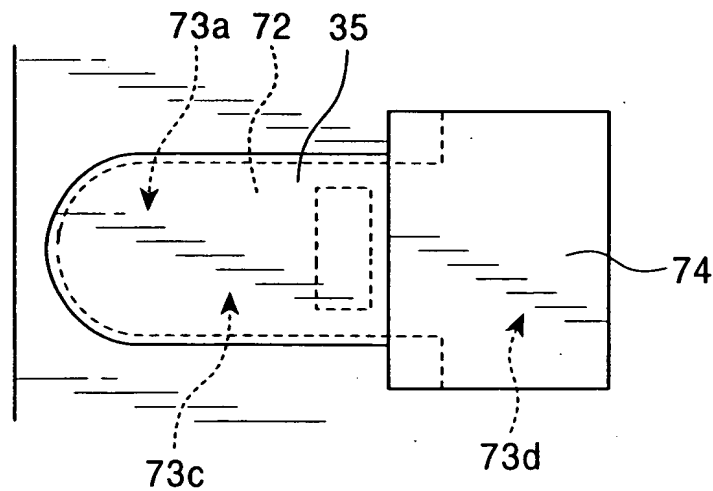
FIG. 11



A cross-sectional view of a semiconductor device. The device consists of a substrate 12, a first conductive layer 21, a second conductive layer 26, and a third conductive layer 25. The substrate 12 is the base layer, followed by the first conductive layer 21, then the second conductive layer 26. The third conductive layer 25 is a rectangular block on top of the second conductive layer 26. A coordinate system (X, Y, Z) is shown on the right, with Z pointing up, Y pointing right, and X pointing out of the page (indicated by a circle with a cross).

[illegible]

Diagram illustrating a cross-sectional view of a semiconductor device. The structure includes a substrate 21, a thin layer 26, and a series of layers and structures formed on top: a layer 12, a layer 27, a layer 25a, a layer 25, a layer 32, a layer 31, a layer 31a, a layer 32, a layer 27, and a layer 33. A cross-hatched region 33a is also shown.



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FIG. 17

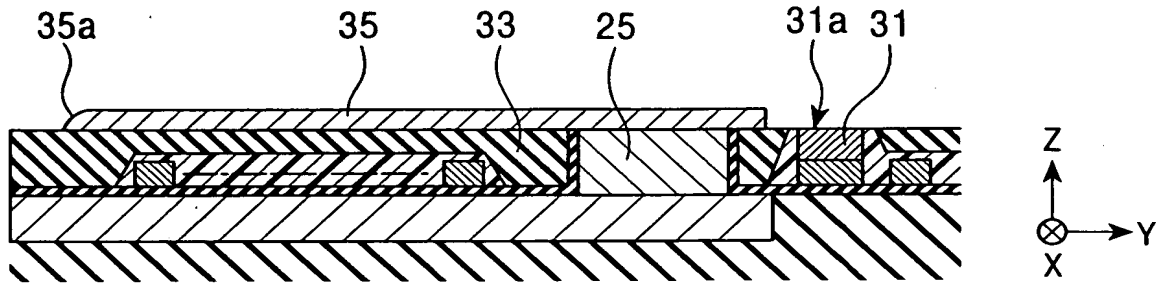
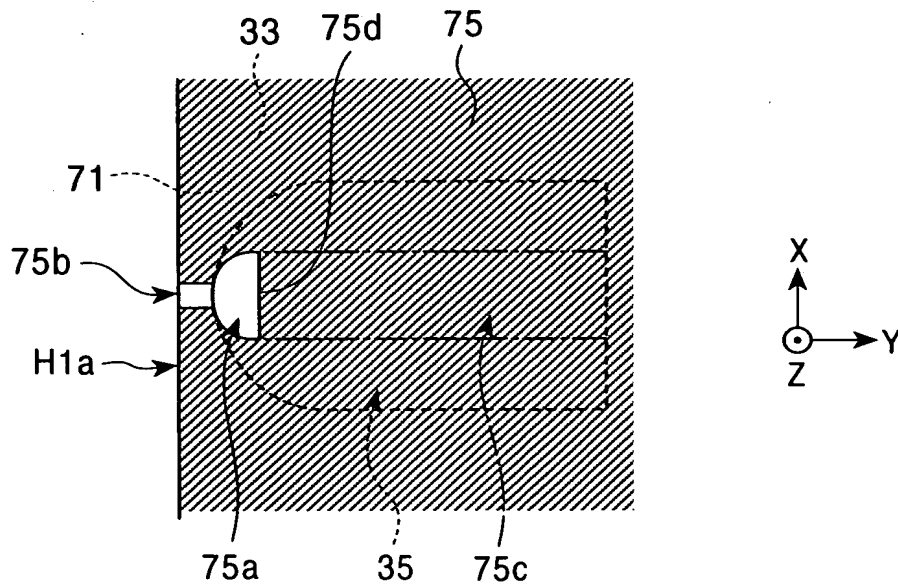


FIG. 18



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FIG. 19

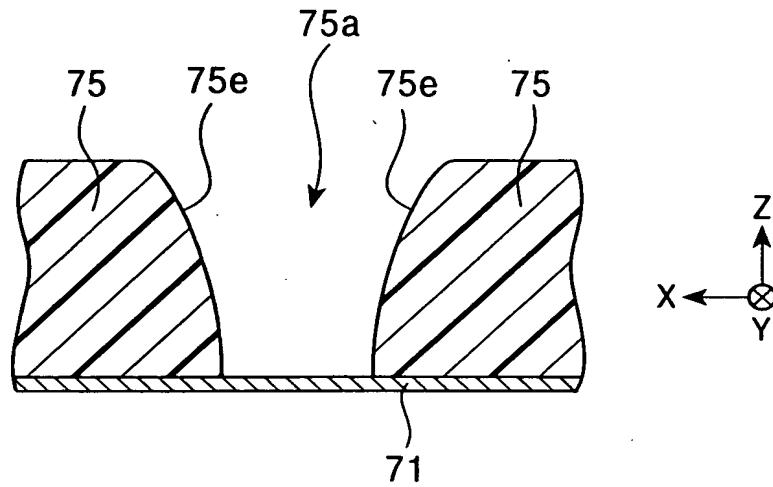
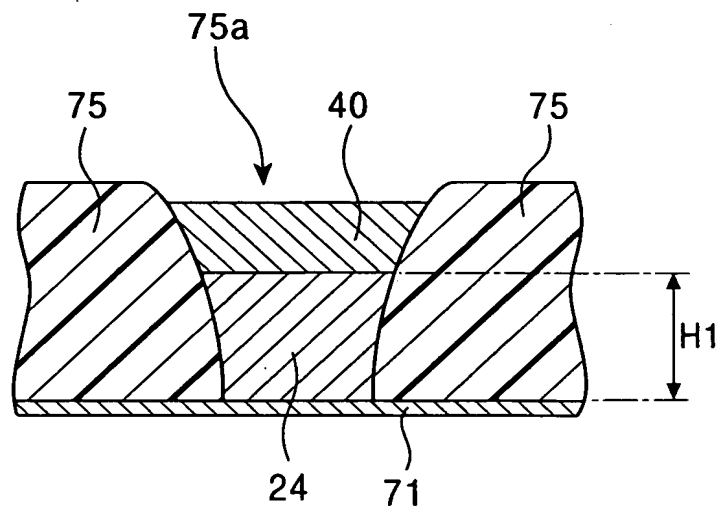


FIG. 20



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FIG. 21

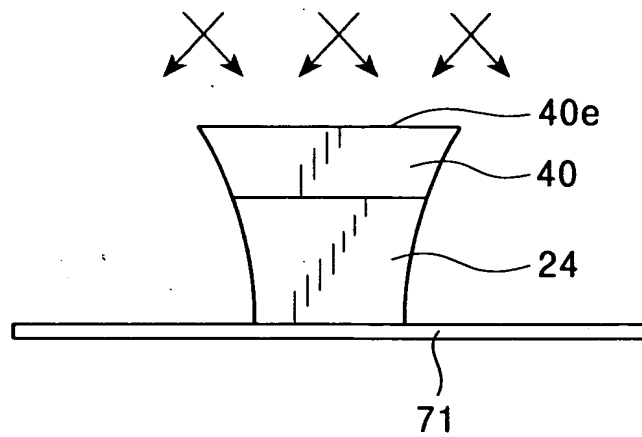
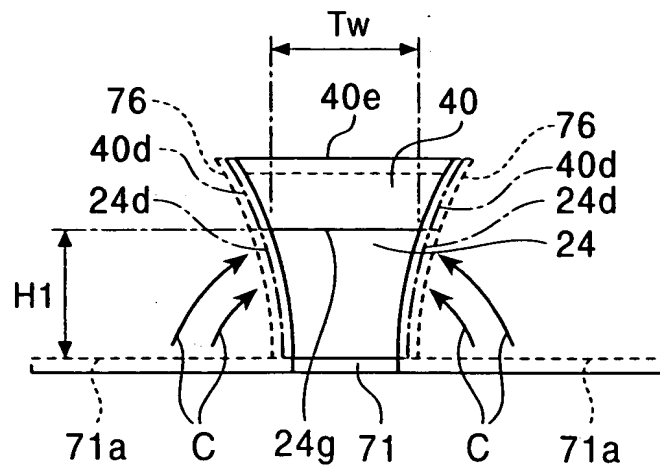


FIG. 22



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FIG. 23

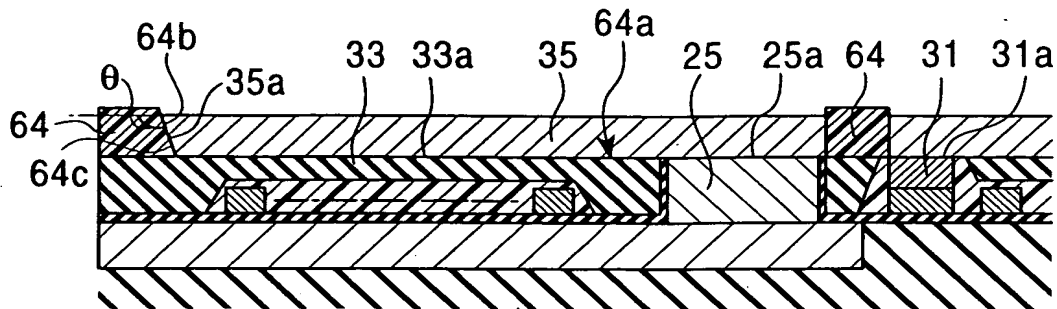


FIG. 24

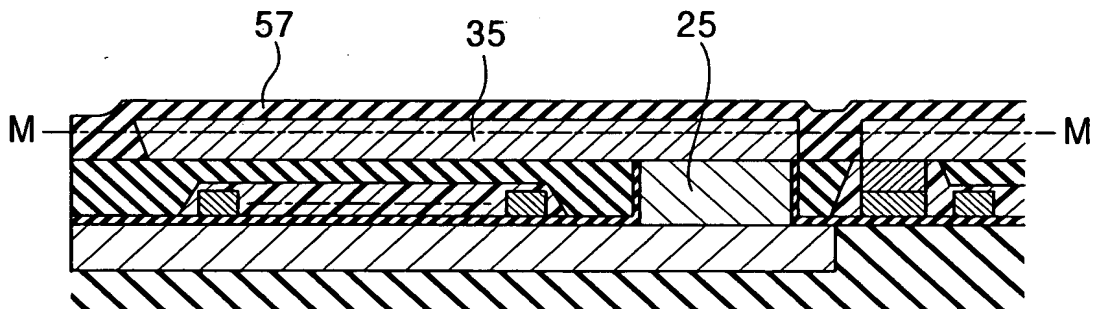
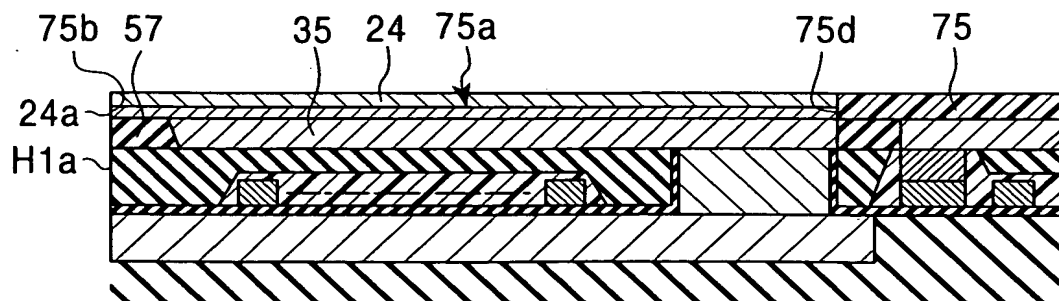
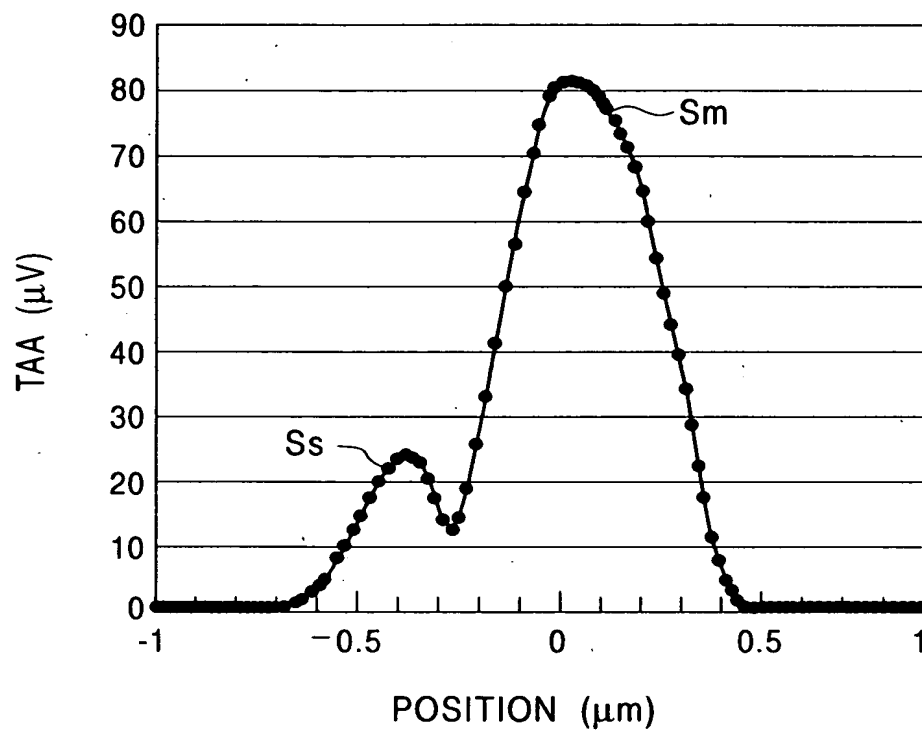


FIG. 25



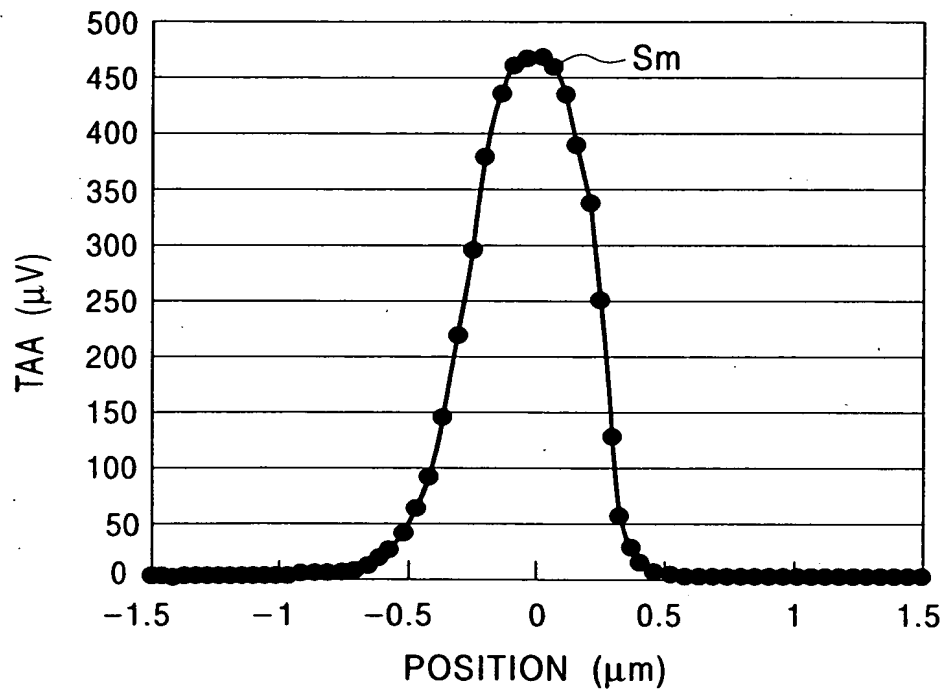
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FIG. 26



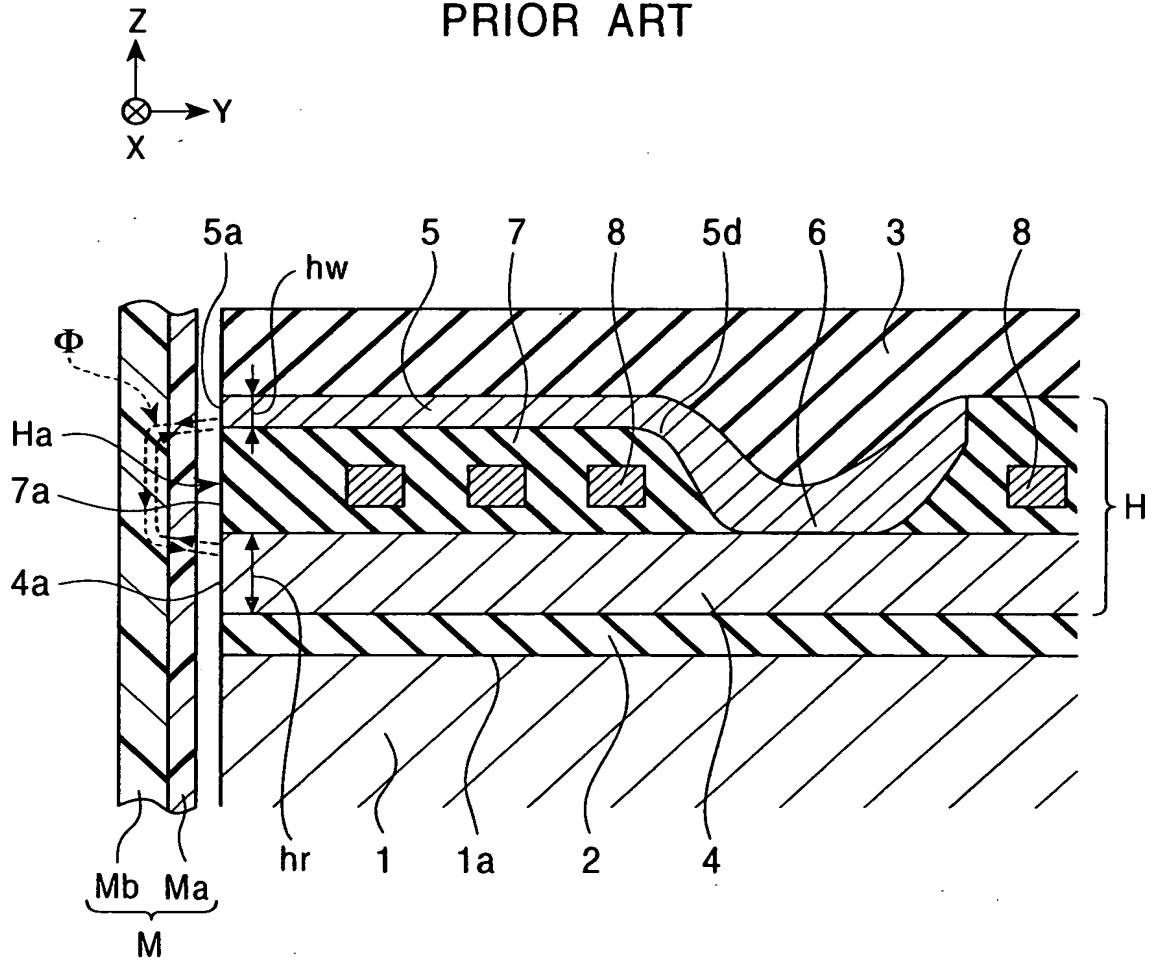
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FIG. 27



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FIG. 28
PRIOR ART



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FIG. 29
PRIOR ART

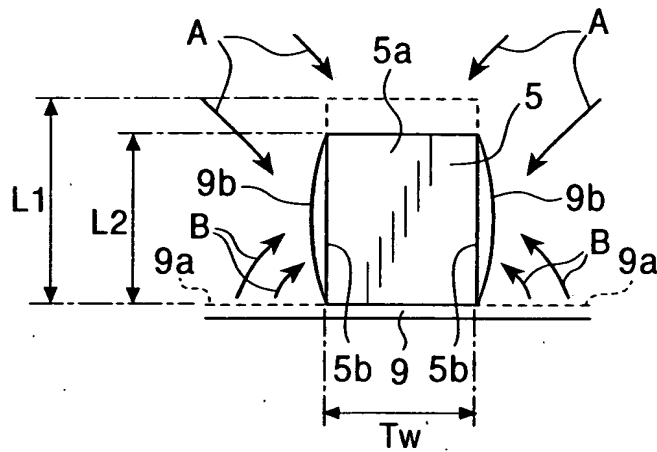


FIG. 30
PRIOR ART

